AMENDMENTS TO THE CLAIMS:

This listing of claims will replace all prior versions, and listings, of claims in the application:

LISTING OF CLAIMS:

1-10 (Canceled)

11. (New) An electrical pressure contact spring of electrically conductive wire, with
- a first contacting region for contacting a first electrically conductive contact pad, a rounded contact tip being arranged in the first contacting region for contacting the contact pad, and
- the contact tip having an outer radius (R) which corresponds to one to three times the thickness of the wire (a),
- a second contacting region for contacting a second electrically conductive contact pad, and
- a compressing region, with at least one wire curvature, arranged between the first contacting region and the second contacting region,

a straight piece of wire extending from the compressing region and finishing in the contact tip running in the direction of the spring force (F), wherein
- the wire is bent in the first contacting region, and wherein
- this wire bend forms the contact tip.

12. (New) The pressure contact spring as claimed in claim 11, wherein
- the wire has a rectangular cross section with a thickness (a) and a depth (b), and in that

– the spring is bent in a plane perpendicular to the depth (b).

13. (New) An electrical contact arrangement, comprising

– a first electrically conductive contact pad,

– a second electrically conductive contact pad, and

– an electrically conductive connection between the first and second contact pads,

the two contact pads being arranged opposite each other and the connection being an electrical contact spring clamped between the two contact pads as claimed in claim 11.

14. (New) The contact arrangement as claimed in claim 13, wherein

– the first contact pad has a hardness of from 45 to 70 Hv, and wherein the spring force (F) lies between 4 and 12 N.

15. (New) The contact arrangement as claimed in claim 13, wherein

– the contact arrangement comprises means by which the contact tip of the pressure contact spring is prevented from penetrating through the first contact pad when it penetrates into said first contact pad.

16. (New) The contact arrangement as claimed in claim 15, wherein

– the means comprise a multilayered first contact pad, a barrier layer which consists of a harder material than the material of a surface layer, the barrier layer being arranged under said surface layer.

17. (New) The contact arrangement as claimed in claim 16, wherein

– the barrier layer has clearances which are filled with the material of the surface layer.

18. (New) A power semiconductor module, comprising

– at least one power semiconductor chip with at least one electrode with a metallization, and

– at least one electrical contact arrangement as claimed in claim 13, the electrode metallization being the first contact pad of the contact arrangement and a terminal led out from the module being the second contact pad of the contact arrangement.

19. (New) The power semiconductor module as claimed in claim 18, wherein

– the power semiconductor module is filled with an electrically insulating gel in the region between the first and second contact pads.

20. (New) An electrical contact arrangement, comprising

– a first electrically conductive contact pad,

– a second electrically conductive contact pad, and

– an electrically conductive connection between the first and second contact pads,

the two contact pads being arranged opposite each other and the connection being an electrical contact spring clamped between the two contact pads as claimed in claim 12.

21. (New) A power semiconductor module, comprising

– at least one power semiconductor chip with at least one electrode with a metallization, and

- at least one electrical contact arrangement as claimed in claim 14, the electrode metallization being the first contact pad of the contact arrangement and a terminal led out from the module being the second contact pad of the contact arrangement.

22. (New) A power semiconductor module, comprising

- at least one power semiconductor chip with at least one electrode with a metallization, and
- at least one electrical contact arrangement as claimed in claim 15, the electrode metallization being the first contact pad of the contact arrangement and a terminal led out from the module being the second contact pad of the contact arrangement.

23. (New) A power semiconductor module, comprising

- at least one power semiconductor chip with at least one electrode with a metallization, and
- at least one electrical contact arrangement as claimed in claim 16, the electrode metallization being the first contact pad of the contact arrangement and a terminal led out from the module being the second contact pad of the contact arrangement.

24. (New) A power semiconductor module, comprising

- at least one power semiconductor chip with at least one electrode with a metallization, and
- at least one electrical contact arrangement as claimed in claim 17,

the electrode metallization being the first contact pad of the contact arrangement and a terminal led out from the module being the second contact pad of the contact arrangement.